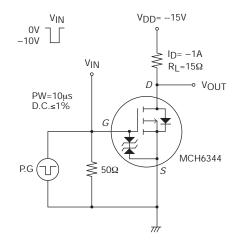
#### Electrical Characteristics at Ta=25°C

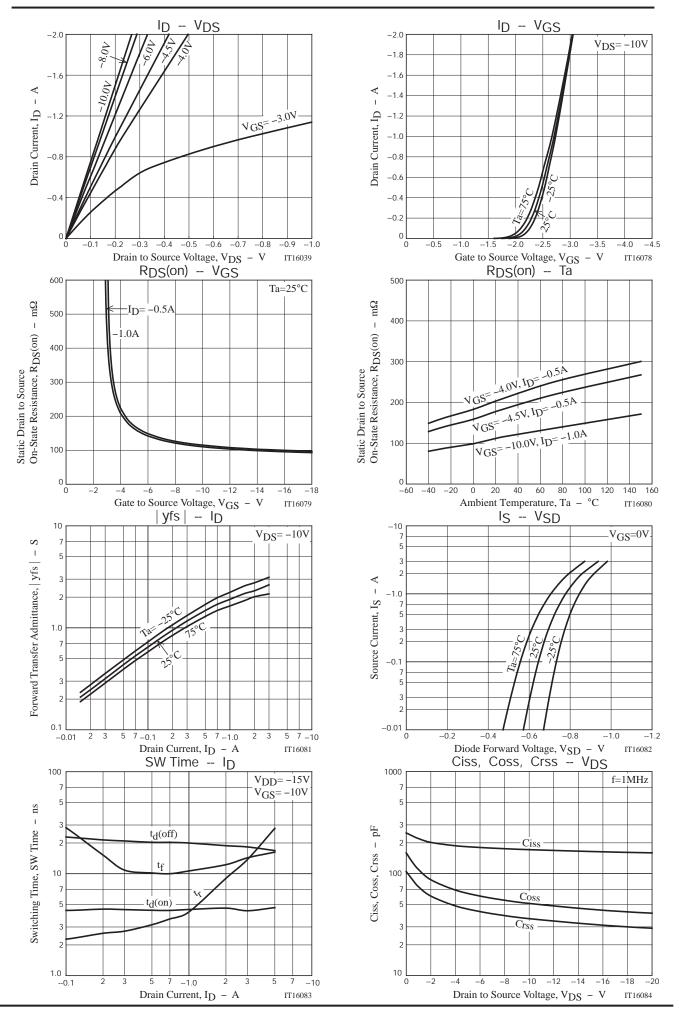
Parameter	Symbol	Conditions	Ratings			Unit
Parameter		Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-30			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V			-1	μΑ
Gate to Source Leakage Current	IGSS	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μΑ
Cutoff Voltage	V <sub>GS</sub> (off)	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1mA -1.2			-2.6	V
Forward Transfer Admittance	yfs	V <sub>D</sub> S=-10V, I <sub>D</sub> =-1A		1.9		S
Static Drain to Source On-State Resistance	R <sub>DS</sub> (on)1	I <sub>D</sub> =-1A, V <sub>G</sub> S=-10V		115	150	mΩ
	R <sub>DS</sub> (on)2	I <sub>D</sub> =-0.5A, V <sub>G</sub> S=-4.5V		182	255	mΩ
	R <sub>DS</sub> (on)3	I <sub>D</sub> =-0.5A, V <sub>G</sub> S=-4V		208	292	mΩ
Input Capacitance	Ciss			172		pF
Output Capacitance	Coss	V <sub>DS</sub> =-10V, f=1MHz		51		pF
Reverse Transfer Capacitance	Crss			36		pF
Turn-ON Delay Time	t <sub>d</sub> (on)			4.5		ns
Rise Time	t <sub>r</sub>	Considered Took Classick		4.2		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.		20		ns
Fall Time	t <sub>f</sub>			10.6		ns
Total Gate Charge	Qg			3.9		nC
Gate to Source Charge	Qgs	V <sub>DS</sub> =-15V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-2A		0.6		nC
Gate to Drain "Miller" Charge	Qgd	]		0.8		nC
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-2A, V <sub>GS</sub> =0V		-0.86	-1.5	V

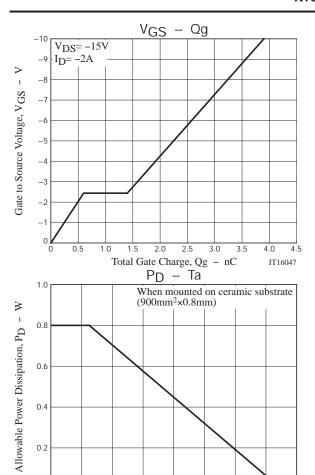
# Switching Time Test Circuit

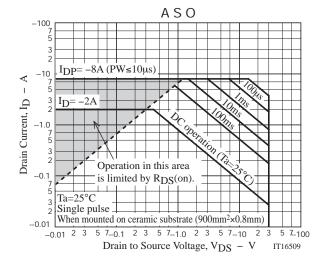


# **Ordering Information**

Device	Package	Shipping	memo
MCH6344-TL-H	MCPH6	3,000pcs./reel	Pb-Free and Halogen Free







0.2

0 L

20

60

80

Ambient Temperature, Ta - °C

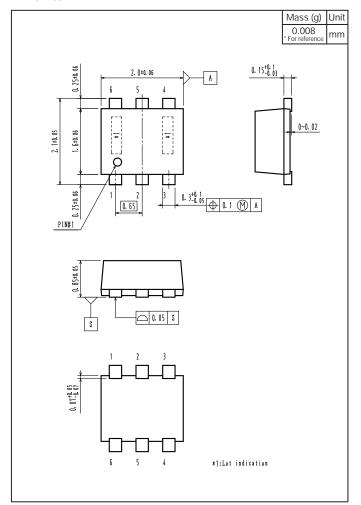
100

140

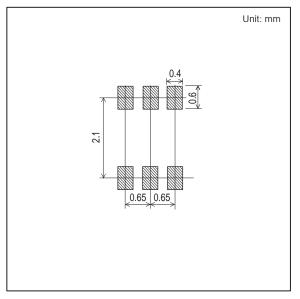
160

IT16510

## Outline Drawing MCH6344-TL-H



## **Land Pattern Example**



Note on usage: Since the MCH6344 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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